

NTD4959N-35G Information



For Reference Only

Part Number NTD4959N-35G **Manufacturer** ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 30V 9A IPAK**Package**TO-251-3 Stub Leads, IPak

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTD4959N-35G Specifications

Manufacturer Part Number NTD4959N-35G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Stub Leads, IPak Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 9A (Ta), 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 11.5V Vgs(th) (Max) @ Id 2.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 25nC @ 11.5V Input Capacitance (Ciss) (Max) @ Vds 1456pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-251-3 Stub Leads, IPakSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C9A (Ta), 58A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 11.5VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 11.5VInput Capacitance (Ciss) (Max) @ Vds1456pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package1-PakPackage / CaseTO-251-3 Stub Leads, IPak	Manufacturer Part Number	NTD4959N-35G
Package TO-251-3 Stub Leads, IPak Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 9A (Ta), 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 11.5V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 25nC @ 11.5V Input Capacitance (Ciss) (Max) @ Vds 1456pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 9 mohm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Manufacturer	ON Semiconductor
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 9A (Ta), 58A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 11.5V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 25nC @ 11.5V Input Capacitance (Ciss) (Max) @ Vds 1456pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package Package / Case N-Cannel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 30V 20V 9A (Ta), 58A (Tc) 9A (Ta), 58A (Tc) 9A (Ta), 58A (Tc) 9A (Ta), 58A (Tc) 1.5V 2.5V @ 250μA 2.5V @ 250μA 2.5V @ 250μA 2.5V @ 250μA 2.5V @ 21.5V 1.456pF @ 12V 2.5V @ 1.5V 1.3W (Ta), 52W (Tc) 9 mOhm @ 30A, 10V 1.3W (Ta), 52W (Tc) 1	Package	TO-251-3 Stub Leads, IPak
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C9A (Ta), 58A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 11.5VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 11.5VInput Capacitance (Ciss) (Max) @ Vds1456pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	Series	-
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Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) 4.5V, 11.5V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 1456pF @ 12V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Perating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 9A (Ta), 58A (Tc) 1.5V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 11.5VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 11.5VInput Capacitance (Ciss) (Max) @ Vds1456pF @ 12VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	Drain to Source Voltage (Vdss)	30V
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Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1456pF @ 12V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 11.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Vgs(th) (Max) @ Id	2.5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	Gate Charge (Qg) (Max) @ Vgs	25nC @ 11.5V
FET Feature - Power Dissipation (Max) 1.3W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Input Capacitance (Ciss) (Max) @ Vds	1456pF @ 12V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Stub Leads, IPak	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Power Dissipation (Max)	1.3W (Ta), 52W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Rds On (Max) @ Id, Vgs	9 mOhm @ 30A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Stub Leads, IPak	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Stub Leads, IPak	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Stub Leads, IPak
		Report errors?

NTD4959N-35G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD4959N-35G Payment Methods



















NTD4959N-35G Shipping Methods













If you have any question about NTD4959N-35G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com